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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/769,835	02/02/2004	Srinath Krishnan	039153-0694	9075
26371 75	90 07/12/2006		EXAMINER	
FOLEY & LARDNER LLP 777 EAST WISCONSIN AVENUE MILWAUKEE, WI 53202-5306			MENZ, DOUGLAS M	
			ART UNIT	PAPER NUMBER
			2891	
		DATE MAILED: 07/12/2006		

Please find below and/or attached an Office communication concerning this application or proceeding.

•	Application No	Applicant(s)
	10/769,835	KRISHNAN, SRINATH
Office Action Summar	y Examiner	Art Unit
	Douglas M. Mer	nz 2891
The MAILING DATE of this con Period for Reply	nmunication appears on the cove	er sheet with the correspondence address —
WHICHEVER IS LONGER, FROM TI - Extensions of time may be available under the pro after SIX (6) MONTHS from the mailing date of this	HE MAILING DATE OF THIS Convisions of 37 CFR 1.136(a). In no event, how a communication.  The statutory period will apply and will expire to reply will, by statute, cause the application on the after the mailing date of this communication.	wever, may a reply be timely filed e SIX (6) MONTHS from the mailing date of this communication. to become ABANDONED (35 U.S.C. § 133).
Status		
1) Responsive to communication(	s) filed on <u>13 March 2006</u> .	
2a) This action is <b>FINAL</b> .	2b)⊠ This action is non-fir	nal.
3)☐ Since this application is in cond	lition for allowance except for fo	ormal matters, prosecution as to the merits is
closed in accordance with the p	practice under Ex parte Quayle,	, 1935 C.D. 11, 453 O.G. 213.
Disposition of Claims		
4)	and 21-24 is/are withdrawn fron	
Application Papers		
9)☐ The specification is objected to	by the Examiner.	
		ed or b)⊡ objected to by the Examiner.
		ld in abeyance. See 37 CFR 1.85(a).
-		the drawing(s) is objected to. See 37 CFR 1.121(d) ne attached Office Action or form PTO-152.
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a calcalcalcalcalcalcalcalcalcalcalcalcalc		
	-	ceived in Application No
3. Copies of the certified co	pies of the priority documents t	have been received in this National Stage
application from the Inter	national Bureau (PCT Rule 17.	.2(a)).
* See the attached detailed Office	action for a list of the certified of	copies not received.
Attachment(s)  1) Notice of References Cited (PTO-892)	٨٢	Interview Summary (PTO-413)
<ul> <li>2) Notice of References Cited (P10-692)</li> <li>2) Notice of Draftsperson's Patent Drawing Rev</li> </ul>		Paper No(s)/Mail Date

U.S. Patent and Trademark Office PTOL-326 (Rev. 7-05)

Paper No(s)/Mail Date \_\_

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

5) Notice of Informal Patent Application (PTO-152)

6) Other: \_\_\_\_.

#### **DETAILED ACTION**

#### Declaration

The declaration filed on 3/13/06 under 37 CFR 1.131 is sufficient to overcome the Efferenn et al. (US 6770530) reference.

# Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-5 are rejected under 35 U.S.C. 102(b) as being anticipated by Park et al. (US 6482715).

Regarding claim 1, Park discloses a method of manufacturing an integrated circuit having trench isolation regions in a substrate, the method comprising:

Forming a mask layer (104, Fig. 3A) above the substrate;

Selectively etching the mask layer to form apertures associated with locations of the trench isolation regions (104, Fig. 3A);

Forming trenches (106a-b, Fig. 3A) in the substrate at the locations;

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Forming first type liners (108, Figs. 3E-G) on first side walls of the trenches associated with first type regions of the substrate (Col. 4); and

Forming second type liners (comprising 108, 110, 112, Figs. 3E-G) on second side walls of the trenches associated with second type regions (Col. 4).

Regarding claim 2, Park further discloses providing an insulative material (116) in the trenches to form trench isolation regions (Figs. 3F-G).

Regarding claim 3, Park further discloses removing the insulative material (116) until a silicon nitride layer (104) is reached (Fig. 3F).

Regarding claim 4, Park further discloses wherein the first type liners are a first thickness and the second type liners are a second thickness, the second thickness being different than the first thickness (Fig. 3G).

Regarding claim 5, Park further discloses wherein the first type liners (108) are dry oxide material (Col. 4) and the second type liners (110) are dry heavily nitrided oxide material (Col. 5).

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### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 6-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Park et al. (US 6482715) in view of Lee et al. (US 6737706).

Regarding claims 6-7, Park discloses the method of claim 1 as mentioned above, however, Park does not explicitly disclose wherein the substrate is on an SOI substrate as in regards to claim 6 or that the substrate trenches reach a buried insulative layer of the substrate as in regards to claim 7. Lee discloses that it is known in the art to form trench isolation features (41) on SOI substrates (30) wherein the trenches reach the buried insulative layer (15) (Fig. 1 and Col. 1). It would have been obvious to one of ordinary skill in the art to implement Park's method with a SOI substrate as taught by Lee because Lee explicitly discloses in the background section that such teachings are conventional.

Regarding claim 8, Park discloses the method of claim 1 as mentioned above and further discloses a first and second region (P and N type), however, Park does not explicitly disclose wherein the substrate includes a strained silicon layer. It would have been obvious to one of ordinary skill in the art at the time the invention was made to

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incorporate Park's teachings with a strained silicon layer because doing so was well known in the art at the time of the invention.

# Response to Arguments

Applicant's arguments with respect to claims 1-8 have been considered but are moot in view of the new ground(s) of rejection.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas M. Menz whose telephone number is 571-272-1877. The examiner can normally be reached on M-F 8-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on 571-272-1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Day by 7/5/06

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